

## DRV5055 比例式线性霍尔效应传感器

### 1 特性

- 比例式线性霍尔效应磁传感器
- 由 3.3V 和 5V 电源供电
- 模拟输出，提供  $V_{CC}/2$  静态失调电压
- 磁性灵敏度选项 ( $V_{CC} = 5V$  时)：
  - A1: 100mV/mT,  $\pm 21mT$  范围
  - A2: 50mV/mT,  $\pm 42mT$  范围
  - A3: 25mV/mT,  $\pm 85mT$  范围
  - A4: 12.5mV/mT,  $\pm 169mT$  范围
- 高速 20kHz 传感带宽
- 低噪声输出，具有  $\pm 1mA$  驱动器
- 磁体温漂补偿
- 标准行业封装：
  - 表面贴装 SOT-23
  - 穿孔 TO-92

### 2 应用

- 精确位置检测
- 工业自动化和机器人
- 家用电器
- 游戏手柄、踏板、键盘、触发器
- 高度找平、倾斜和重量测量
- 流体流速测量
- 医疗设备
- 绝对值角度编码
- 电流检测

### 3 说明

DRV5055 器件是一款线性霍尔效应传感器，可按比例响应磁通量密度。该器件可用于进行精确的位置检测，应用范围广泛低功耗是一个关键问题。

该器件由 3.3V 或 5V 电源供电。当不存在磁场时，模拟输出可驱动  $1/2 V_{CC}$ 。输出会随施加的磁通量密度呈线性变化，四个灵敏度选项可以根据所需的感应范围提供最大的输出电压摆幅。南北磁极产生唯一的电压。

它可检测垂直于封装顶部的磁通量，而且两个封装选项提供不同的检测方向。

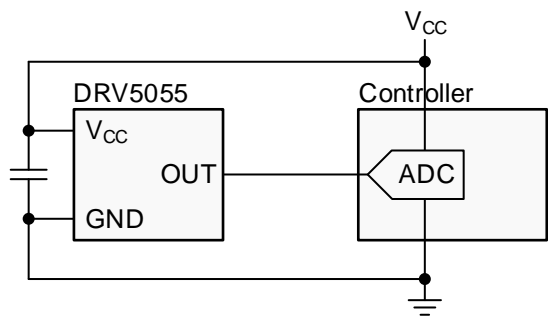
该器件使用比例式架构，当外部模数转换器 (ADC) 使用相同的  $V_{CC}$  作为其基准电压时，可以消除  $V_{CC}$  容差产生的误差。此外，该器件还具有磁体温漂补偿功能，可以抵消磁体漂移，在较宽的  $-40^{\circ}C$  至  $125^{\circ}C$  温度范围内实现线性性能。

器件信息<sup>(1)</sup>

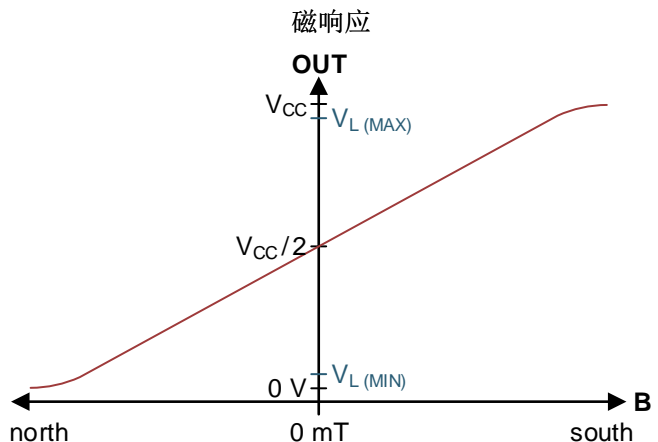
器件型号	封装	封装尺寸 (标称值)
DRV5055	SOT-23 (3)	2.92mm × 1.30mm
	TO-92 (3)	4.00mm × 3.15mm

(1) 要了解所有可用封装，请参阅数据表末尾的可订购产品附录。

典型原理图



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## 目录

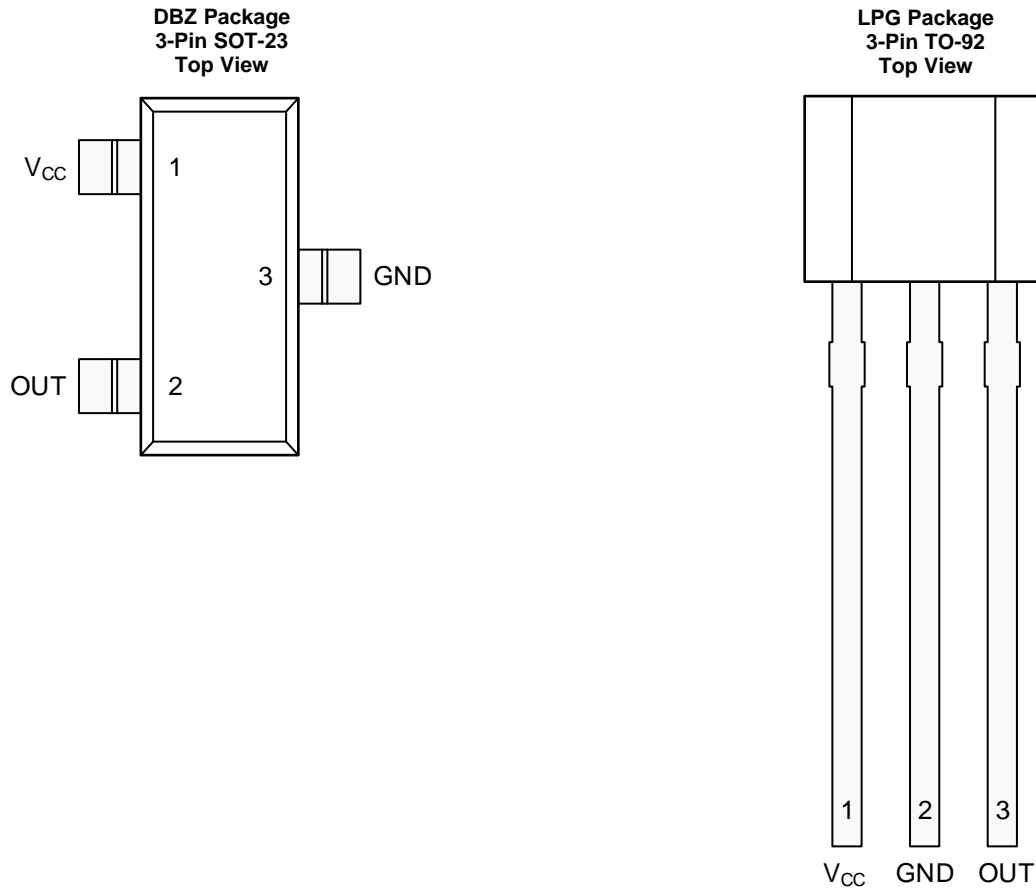
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## 4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

日期	修订版本	说明
2018 年 1 月	*	第一版。

## 5 Pin Configuration and Functions



### Pin Functions

NAME	PIN		I/O	DESCRIPTION
	SOT-23	TO-92		
V <sub>CC</sub>	1	1	—	Power supply. TI recommends connecting this pin to a ceramic capacitor to ground with a value of at least 0.01 $\mu$ F.
OUT	2	3	O	Analog output
GND	3	2	—	Ground reference

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Power supply voltage	V <sub>CC</sub>	−0.3	7	V
Output voltage	OUT	−0.3	V <sub>CC</sub> + 0.3	V
Magnetic flux density, B <sub>MAX</sub>		Unlimited		T
Operating junction temperature, T <sub>J</sub>		−40	150	°C
Storage temperature, T <sub>stg</sub>		−65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2500	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±750	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
$V_{CC}$ Power supply voltage <sup>(1)</sup>		3	3.63	V
		4.5	5.5	
$I_O$ Output continuous current		–1	1	mA
$T_A$ Operating ambient temperature <sup>(2)</sup>		–40	125	°C

(1) There are two isolated operating  $V_{CC}$  ranges. For more information see the [Operating  \$V\_{CC}\$  Ranges](#) section.

(2) Power dissipation and thermal limits must be observed.

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		DRV5055		UNIT
		SOT-23 (DBZ)	TO-92 (LPG)	
		3 PINS	3 PINS	
$R_{\theta JA}$ Junction-to-ambient thermal resistance		170	121	°C/W
$R_{\theta JC(top)}$ Junction-to-case (top) thermal resistance		66	67	°C/W
$R_{\theta JB}$ Junction-to-board thermal resistance		49	97	°C/W
$Y_{JT}$ Junction-to-top characterization parameter		1.7	7.6	°C/W
$Y_{JB}$ Junction-to-board characterization parameter		48	97	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

for  $V_{CC} = 3\text{ V}$  to  $3.63\text{ V}$  and  $4.5\text{ V}$  to  $5.5\text{ V}$ , over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS <sup>(1)</sup>	MIN	TYP	MAX	UNIT
$I_{CC}$ Operating supply current			6	10	mA
$t_{ON}$ Power-on time (see <a href="#">Figure 11</a> )	$B = 0\text{ mT}$ , no load on OUT		175	330	μs
$f_{BW}$ Sensing bandwidth			20		kHz
$t_d$ Propagation delay time	From change in B to change in OUT		10		μs
$B_{ND}$ Input-referred RMS noise density	$V_{CC} = 5\text{ V}$		130		nT/√Hz
	$V_{CC} = 3.3\text{ V}$		215		
$B_N$ Input-referred noise	$B_{ND} \times 6.6 \times \sqrt{20\text{ kHz}}$	$V_{CC} = 5\text{ V}$	0.12		mT <sub>PP</sub>
		$V_{CC} = 3.3\text{ V}$	0.2		
$V_N$ Output-referred noise <sup>(2)</sup>	$B_N \times S$	DRV5055A1	12		mV <sub>PP</sub>
		DRV5055A2	6		
		DRV5055A3	3		
		DRV5055A4	1.5		

(1) B is the applied magnetic flux density.

(2)  $V_N$  describes voltage noise on the device output. If the full device bandwidth is not needed, noise can be reduced with an RC filter.

## 6.6 Magnetic Characteristics

for  $V_{CC} = 3\text{ V}$  to  $3.63\text{ V}$  and  $4.5\text{ V}$  to  $5.5\text{ V}$ , over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS <sup>(1)</sup>		MIN	TYP	MAX	UNIT
$V_Q$	Quiescent voltage	$B = 0\text{ mT}$ , $T_A = 25^\circ\text{C}$	$V_{CC} = 5\text{ V}$	2.43	2.5	2.57	V
			$V_{CC} = 3.3\text{ V}$	1.59	1.65	1.71	
$V_{Q\Delta T}$	Quiescent voltage temperature drift	$B = 0\text{ mT}$ , $T_A = -40^\circ\text{C}$ to $125^\circ\text{C}$ versus $25^\circ\text{C}$		$\pm 1\% \times V_{CC}$			V
$V_{QRE}$	Quiescent voltage ratiometry error <sup>(2)</sup>			$\pm 0.2\%$			
$V_{Q\Delta L}$	Quiescent voltage lifetime drift	High-temperature operating stress for 1000 hours		$< 0.5\%$			
S	Sensitivity	$V_{CC} = 5\text{ V}$ , $T_A = 25^\circ\text{C}$	DRV5055A1	95	100	105	mV/mT
			DRV5055A2	47.5	50	52.5	
			DRV5055A3	23.8	25	26.2	
			DRV5055A4	11.9	12.5	13.2	
		$V_{CC} = 3.3\text{ V}$ , $T_A = 25^\circ\text{C}$	DRV5055A1	57	60	63	
			DRV5055A2	28.5	30	31.5	
			DRV5055A3	14.3	15	15.8	
			DRV5055A4	7.1	7.5	7.9	
$B_L$	Linear magnetic sensing range <sup>(3)(4)</sup>	$V_{CC} = 5\text{ V}$ , $T_A = 25^\circ\text{C}$	DRV5055A1	$\pm 21$			mT
			DRV5055A2	$\pm 42$			
			DRV5055A3	$\pm 85$			
			DRV5055A4	$\pm 169$			
		$V_{CC} = 3.3\text{ V}$ , $T_A = 25^\circ\text{C}$	DRV5055A1	$\pm 22$			
			DRV5055A2	$\pm 44$			
			DRV5055A3	$\pm 88$			
			DRV5055A4	$\pm 176$			
$V_L$	Linear range of output voltage <sup>(4)</sup>			0.2	$V_{CC} - 0.2$		V
$S_{TC}$	Sensitivity temperature compensation for magnets <sup>(5)</sup>				0.12		%/ $^\circ\text{C}$
$S_{LE}$	Sensitivity linearity error <sup>(4)</sup>	$V_{OUT}$ is within $V_L$			$\pm 1\%$		
$S_{SE}$	Sensitivity symmetry error <sup>(4)</sup>	$V_{OUT}$ is within $V_L$			$\pm 1\%$		
$S_{RE}$	Sensitivity ratiometry error <sup>(2)</sup>	$T_A = 25^\circ\text{C}$ , with respect to $V_{CC} = 3.3\text{ V}$ or $5\text{ V}$		$-2.5\%$		2.5%	
$S_{\Delta L}$	Sensitivity lifetime drift	High-temperature operating stress for 1000 hours			$< 0.5\%$		%

(1) B is the applied magnetic flux density.

(2) See the [Ratiometric Architecture](#) section.

(3)  $B_L$  describes the minimum linear sensing range at  $25^\circ\text{C}$  taking into account the maximum  $V_Q$  and Sensitivity tolerances.

(4) See the [Sensitivity Linearity](#) section.

(5)  $S_{TC}$  describes the rate the device increases Sensitivity with temperature. For more information, see the [Sensitivity Temperature Compensation For Magnets](#) section.

## 6.7 Typical Characteristics

for  $T_A = 25^\circ\text{C}$  (unless otherwise noted)

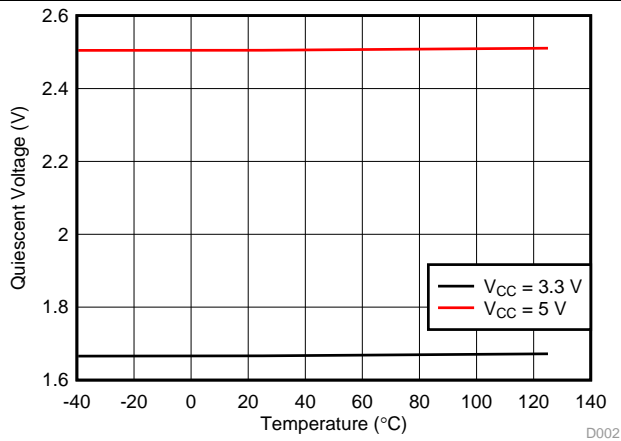


图 1. Quiescent Voltage vs Temperature

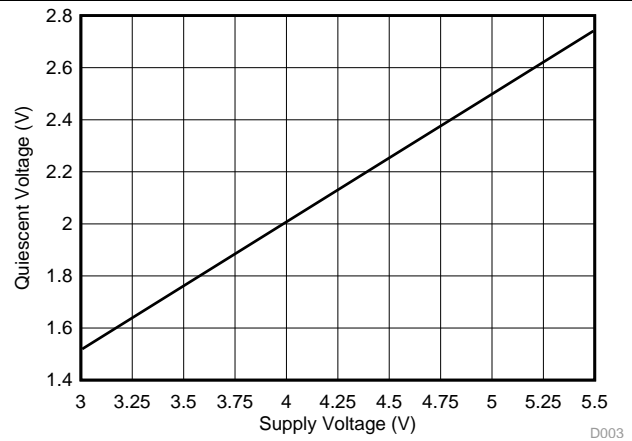


图 2. Quiescent Voltage vs Supply Voltage

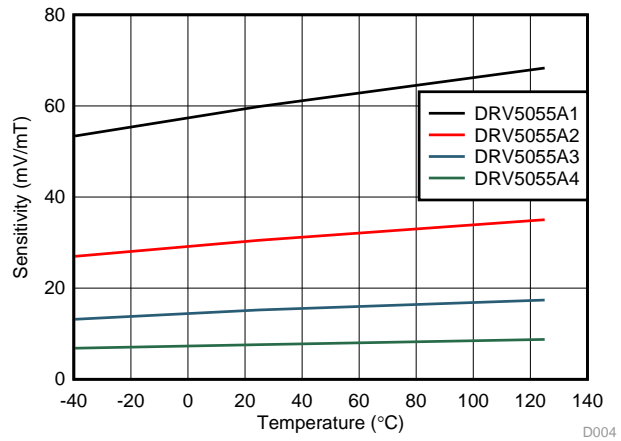


图 3. Sensitivity vs Temperature,  $V_{CC} = 3.3\text{ V}$

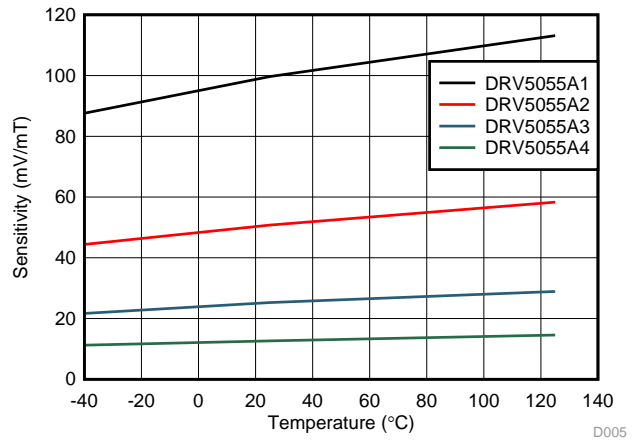


图 4. Sensitivity vs Temperature,  $V_{CC} = 5\text{ V}$

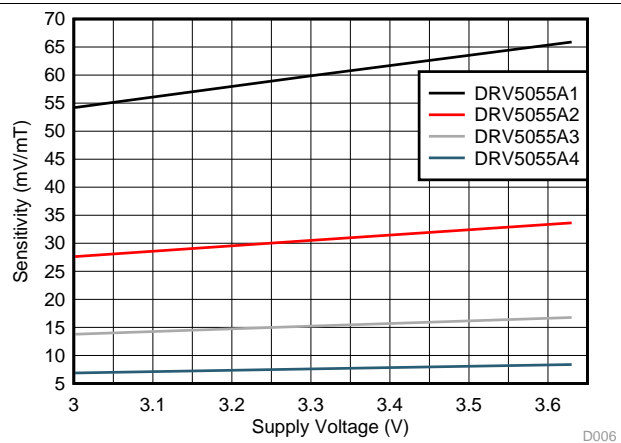


图 5. Sensitivity vs Supply Voltage,  $V_{CC} = 3.3\text{ V} \pm 10\%$

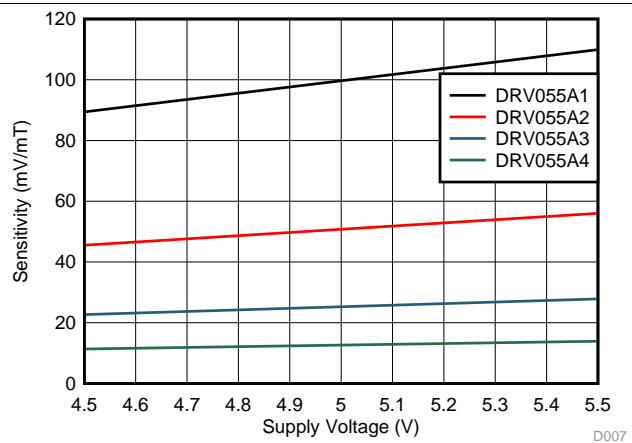


图 6. Sensitivity vs Supply Voltage,  $V_{CC} = 5\text{ V} \pm 10\%$

## Typical Characteristics (接下页)

for  $T_A = 25^\circ\text{C}$  (unless otherwise noted)

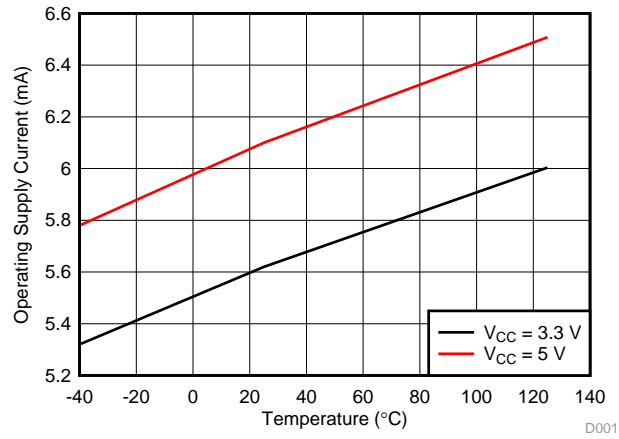


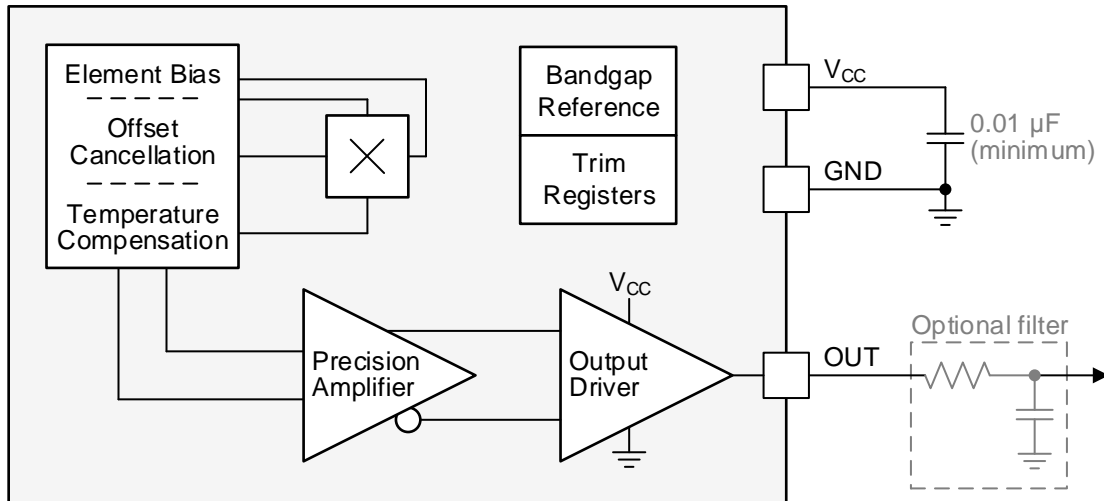
图 7. Operating Supply Current vs Temperature

## 7 Detailed Description

### 7.1 Overview

The DRV5055 is a 3-pin linear Hall effect sensor with fully integrated signal conditioning, temperature compensation circuits, mechanical stress cancellation, and amplifiers. The device operates from 3.3-V and 5-V ( $\pm 10\%$ ) power supplies, measures magnetic flux density, and outputs a proportional analog voltage that is referenced to  $V_{CC}$ .

### 7.2 Functional Block Diagram



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### 7.3 Feature Description

#### 7.3.1 Magnetic Flux Direction

As shown in 图 8, the DRV5055 is sensitive to the magnetic field component that is perpendicular to the top of the package.

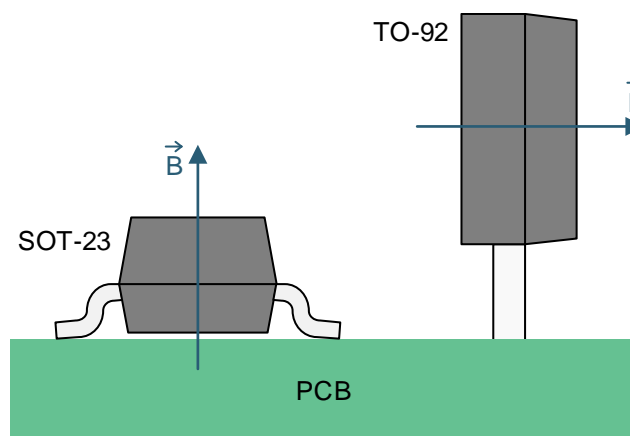


图 8. Direction of Sensitivity



## Feature Description (接下页)

Magnetic flux that travels from the bottom to the top of the package is considered positive in this document. This condition exists when a south magnetic pole is near the top (marked-side) of the package. Magnetic flux that travels from the top to the bottom of the package results in negative millitesla values.

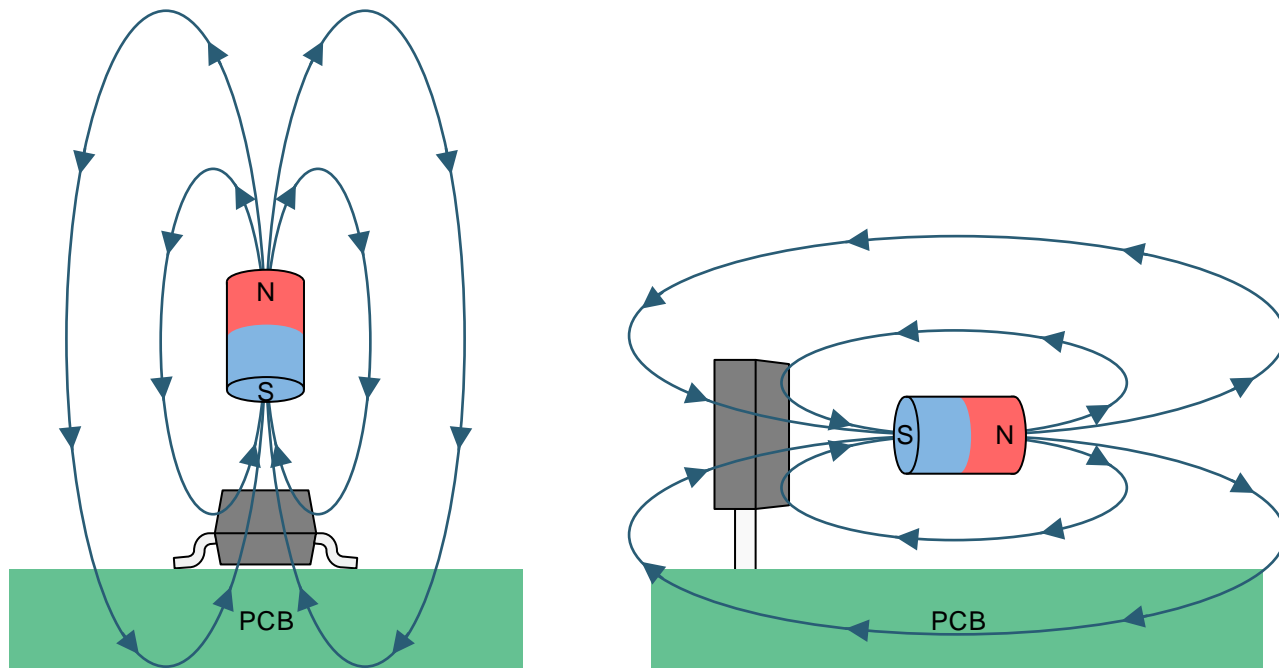


图 9. The Flux Direction for Positive B

### 7.3.2 Magnetic Response

When the DRV5055 is powered, the DRV5055 outputs an analog voltage according to 公式 1:

$$V_{OUT} = V_Q + B \times (\text{Sensitivity}_{(25^\circ\text{C})} \times (1 + S_{TC} \times (T_A - 25^\circ\text{C})))$$

where

- $V_Q$  is typically half of  $V_{CC}$
- $B$  is the applied magnetic flux density
- $\text{Sensitivity}_{(25^\circ\text{C})}$  depends on the device option and  $V_{CC}$
- $S_{TC}$  is typically 0.12%/°C
- $T_A$  is the ambient temperature
- $V_{OUT}$  is within the  $V_L$  range

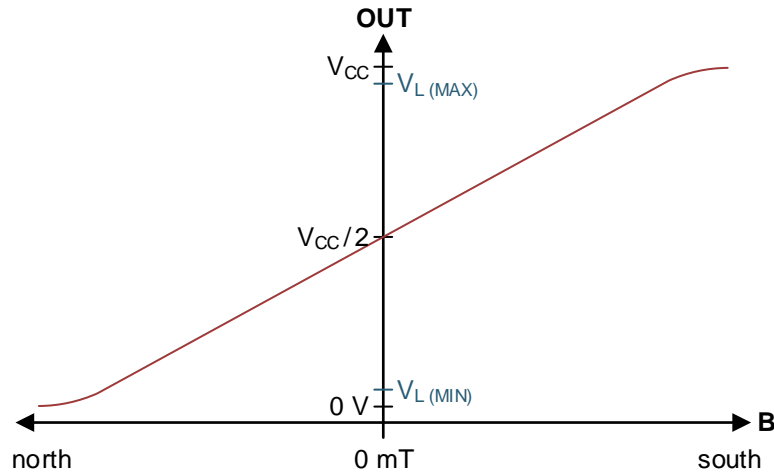
(1)

As an example, consider the DRV5055A3 with  $V_{CC} = 3.3\text{ V}$ , a temperature of  $50^\circ\text{C}$ , and  $67\text{ mT}$  applied. Excluding tolerances,  $V_{OUT} = 1650\text{ mV} + 67\text{ mT} \times (15\text{ mV/mT} \times (1 + 0.0012/^\circ\text{C} \times (50^\circ\text{C} - 25^\circ\text{C}))) = 2685\text{ mV}$ .

### 7.3.3 Sensitivity Linearity

The device produces a linear response when the output voltage is within the specified  $V_L$  range. Outside this range, sensitivity is reduced and nonlinear. 图 10 graphs the magnetic response.

## Feature Description (接下页)



**图 10. Magnetic Response**

**公式 2** calculates parameter  $B_L$ , the minimum linear sensing range at 25°C taking into account the maximum quiescent voltage and sensitivity tolerances.

$$B_{L(MIN)} = \frac{V_{L(MAX)} - V_{Q(MAX)}}{S_{(MAX)}} \quad (2)$$

The parameter  $S_{LE}$  defines linearity error as the difference in sensitivity between any two positive  $B$  values, and any two negative  $B$  values, while the output is within the  $V_L$  range.

The parameter  $S_{SE}$  defines symmetry error as the difference in sensitivity between any positive  $B$  value and the negative  $B$  value of the same magnitude, while the output voltage is within the  $V_L$  range.

### 7.3.4 Ratiometric Architecture

The DRV5055 has a ratiometric analog architecture that scales the quiescent voltage and sensitivity linearly with the power-supply voltage. For example, the quiescent voltage and sensitivity are 5% higher when  $V_{CC} = 5.25$  V compared to  $V_{CC} = 5$  V. This behavior enables external ADCs to digitize a consistent value regardless of the power-supply voltage tolerance, when the ADC uses  $V_{CC}$  as its reference.

**公式 3** calculates sensitivity ratiometry error:

$$S_{RE} = 1 - \frac{S_{(VCC)} / S_{(5V)}}{V_{CC} / 5V} \quad \text{for } V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}, \quad S_{RE} = 1 - \frac{S_{(VCC)} / S_{(3.3V)}}{V_{CC} / 3.3V} \quad \text{for } V_{CC} = 3 \text{ V to } 3.63 \text{ V}$$

where

- $S_{(VCC)}$  is the sensitivity at the current  $V_{CC}$  voltage
  - $S_{(5V)}$  or  $S_{(3.3V)}$  is the sensitivity when  $V_{CC} = 5$  V or 3.3 V
  - $V_{CC}$  is the current  $V_{CC}$  voltage
- (3)

**公式 4** calculates quiescent voltage ratiometry error:

$$V_{QRE} = 1 - \frac{V_{Q(VCC)} / V_{Q(5V)}}{V_{CC} / 5V} \quad \text{for } V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}, \quad V_{QRE} = 1 - \frac{V_{Q(VCC)} / V_{Q(3.3V)}}{V_{CC} / 3.3V} \quad \text{for } V_{CC} = 3 \text{ V to } 3.63 \text{ V}$$

where

- $V_{Q(VCC)}$  is the quiescent voltage at the current  $V_{CC}$  voltage
  - $V_{Q(5V)}$  or  $V_{Q(3.3V)}$  is the quiescent voltage when  $V_{CC} = 5$  V or 3.3 V
  - $V_{CC}$  is the current  $V_{CC}$  voltage
- (4)

## Feature Description (接下页)

### 7.3.5 Operating $V_{CC}$ Ranges

The DRV5055 has two recommended operating  $V_{CC}$  ranges: 3 V to 3.63 V and 4.5 V to 5.5 V. When  $V_{CC}$  is in the middle region between 3.63 V to 4.5 V, the device continues to function, but sensitivity is less known because there is a crossover threshold near 4 V that adjusts device characteristics.

### 7.3.6 Sensitivity Temperature Compensation For Magnets

Magnets generally produce weaker fields as temperature increases. The DRV5055 compensates by increasing sensitivity with temperature, as defined by the parameter  $S_{TC}$ . The sensitivity at  $T_A = 125^\circ\text{C}$  is typically 12% higher than at  $T_A = 25^\circ\text{C}$ .

### 7.3.7 Power-On Time

After the  $V_{CC}$  voltage is applied, the DRV5055 requires a short initialization time before the output is set. The parameter  $t_{ON}$  describes the time from when  $V_{CC}$  crosses 3 V until OUT is within 5% of  $V_Q$ , with 0 mT applied and no load attached to OUT. 图 11 shows this timing diagram.

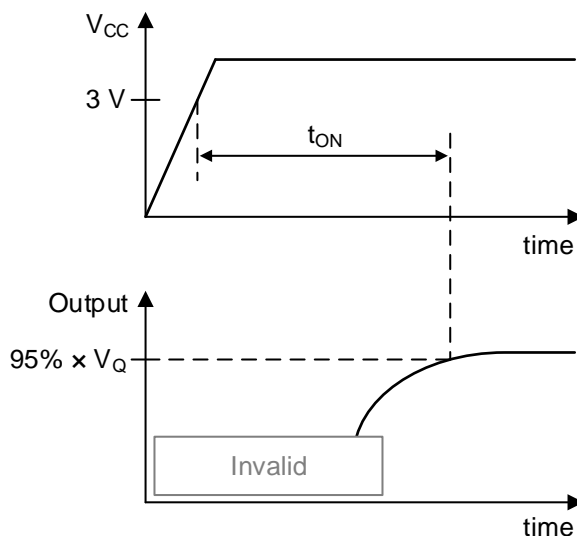


图 11.  $t_{ON}$  Definition

## Feature Description (接下页)

### 7.3.8 Hall Element Location

图 12 shows the location of the sensing element inside each package option.

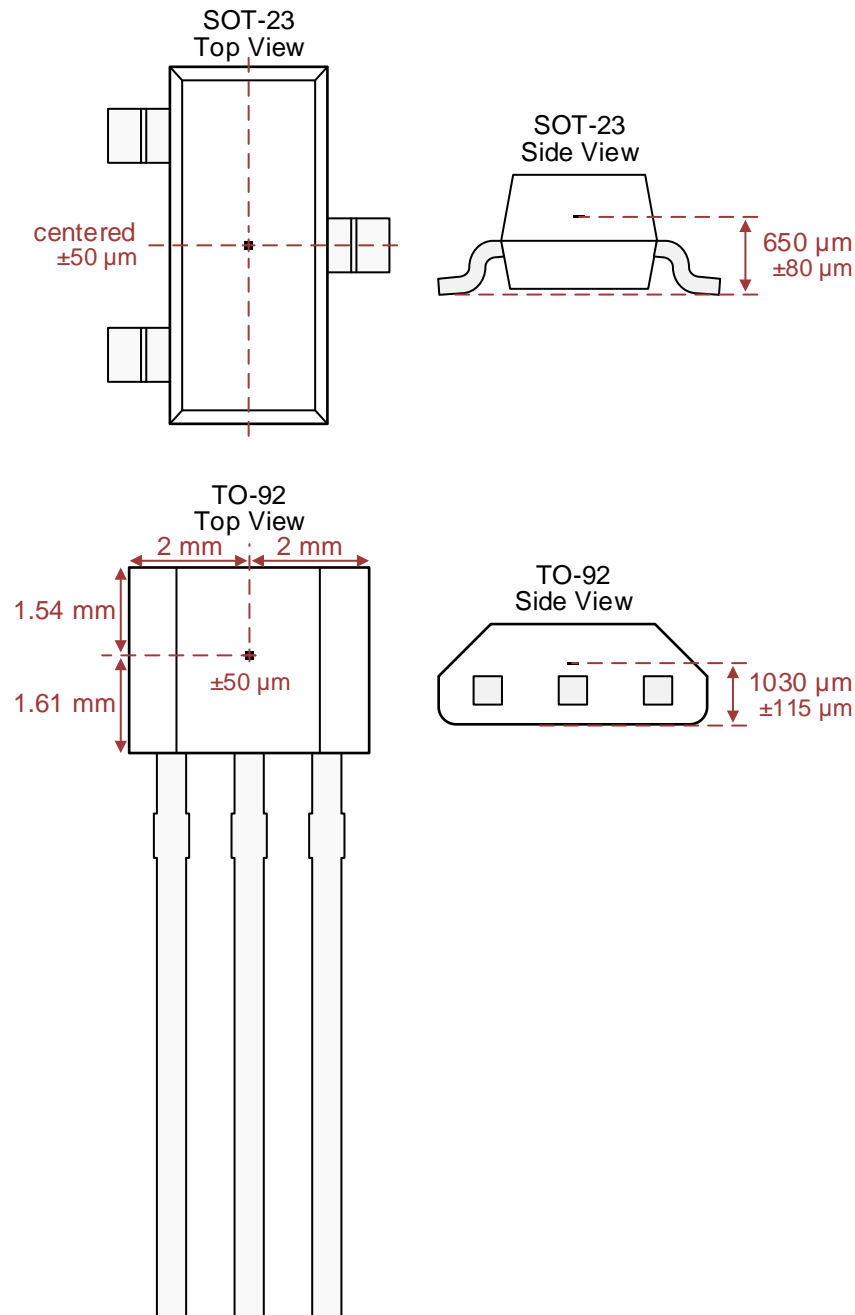


图 12. Hall Element Location

## 7.4 Device Functional Modes

The DRV5055 has one mode of operation that applies when the *Recommended Operating Conditions* are met.

## 8 Application and Implementation

### 注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

#### 8.1.1 Selecting the Sensitivity Option

Select the highest DRV5055 sensitivity option that can measure the required range of magnetic flux density, so that the output voltage swing is maximized.

Larger-sized magnets and farther sensing distances can generally enable better positional accuracy than very small magnets at close distances, because magnetic flux density increases exponentially with the proximity to a magnet. TI created an online tool to help with simple magnet calculations at <http://www.ti.com/product/drv5013>.

#### 8.1.2 Temperature Compensation for Magnets

The DRV5055 temperature compensation is designed to directly compensate the average drift of neodymium (NdFeB) magnets and partially compensate ferrite magnets. The residual induction ( $B_r$ ) of a magnet typically reduces by 0.12%/°C for NdFeB, and 0.20%/°C for ferrite. When the operating temperature of a system is reduced, temperature drift errors are also reduced.

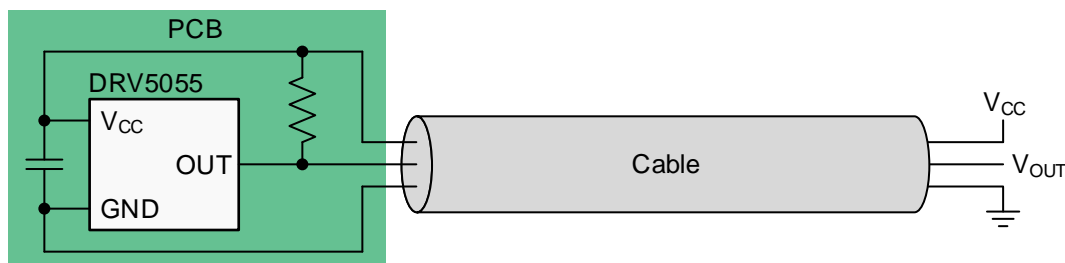
#### 8.1.3 Adding a Low-Pass Filter

As shown in the [Functional Block Diagram](#), an RC low-pass filter can be added to the device output for the purpose of minimizing voltage noise when the full 20-kHz bandwidth is not needed. This filter can improve the signal-to-noise ratio (SNR) and overall accuracy. Do not connect a capacitor directly to the device output without a resistor in between because doing so can make the output unstable.

#### 8.1.4 Designing for Wire Break Detection

Some systems must detect if interconnect wires become open or shorted. The DRV5055 can support this function.

First, select a sensitivity option that causes the output voltage to stay within the  $V_L$  range during normal operation. Second, add a pullup resistor between OUT and  $V_{CC}$ . TI recommends a value between 20 k $\Omega$  to 100 k $\Omega$ , and the current through OUT must not exceed the  $I_O$  specification, including current going into an external ADC. Then, if the output voltage is ever measured to be within 150 mV of  $V_{CC}$  or GND, a fault condition exists. 图 13 shows the circuit, and 表 1 describes fault scenarios.



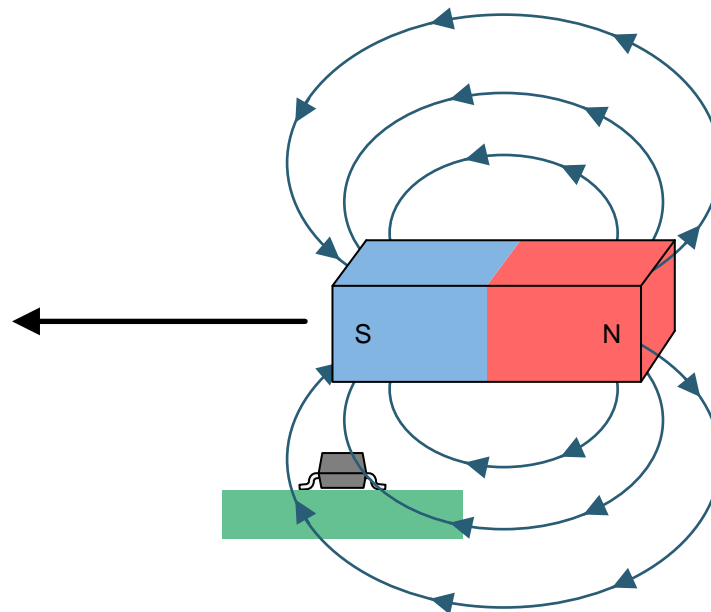
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图 13. Wire Fault Detection Circuit

**表 1. Fault Scenarios and the Resulting  $V_{OUT}$**

FAULT SCENARIO	$V_{OUT}$
$V_{CC}$ disconnects	Close to GND
GND disconnects	Close to $V_{CC}$
$V_{CC}$ shorts to OUT	Close to $V_{CC}$
GND shorts to OUT	Close to GND

## 8.2 Typical Application



**图 14. Common Magnet Orientation**

### 8.2.1 Design Requirements

Use the parameters listed in 表 2 for this design example.

**表 2. Design Parameters**

DESIGN PARAMETER	EXAMPLE VALUE
$V_{CC}$	5 V
Magnet	15 × 5 × 5 mm NdFeB
Travel distance	12 mm
Maximum B at the sensor at 25°C	±75 mT
Device option	DRV5055A3

### 8.2.2 Detailed Design Procedure

Linear Hall effect sensors provide flexibility in mechanical design, because many possible magnet orientations and movements produce a usable response from the sensor. 图 14 shows one of the most common orientations, which uses the full north to south range of the sensor and causes a close-to-linear change in magnetic flux density as the magnet moves across.

When designing a linear magnetic sensing system, always consider these three variables: the magnet, sensing distance, and the range of the sensor. Select the DRV5055 with the highest sensitivity that has a  $B_L$  (linear magnetic sensing range) that is larger than the maximum magnetic flux density in the application. To determine the magnetic flux density the sensor receives, TI recommends using magnetic field simulation software, referring to magnet specifications, and testing.

### 8.2.3 Application Curve

图 15 shows the simulated magnetic flux from a NdFeB magnet.

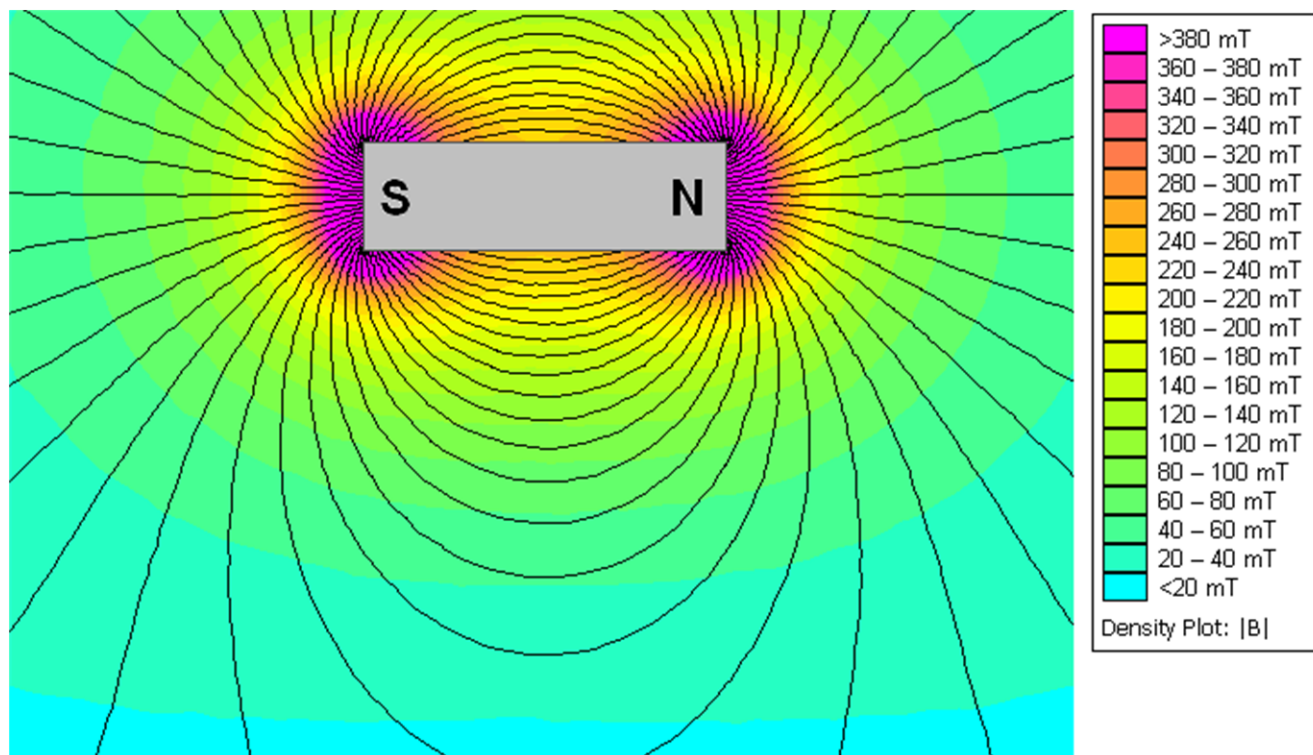


图 15. Simulated Magnetic Flux

### 8.3 Do's and Don'ts

Because the Hall element is sensitive to magnetic fields that are perpendicular to the top of the package, a correct magnet approach must be used for the sensor to detect the field. 图 16 shows correct and incorrect approaches.

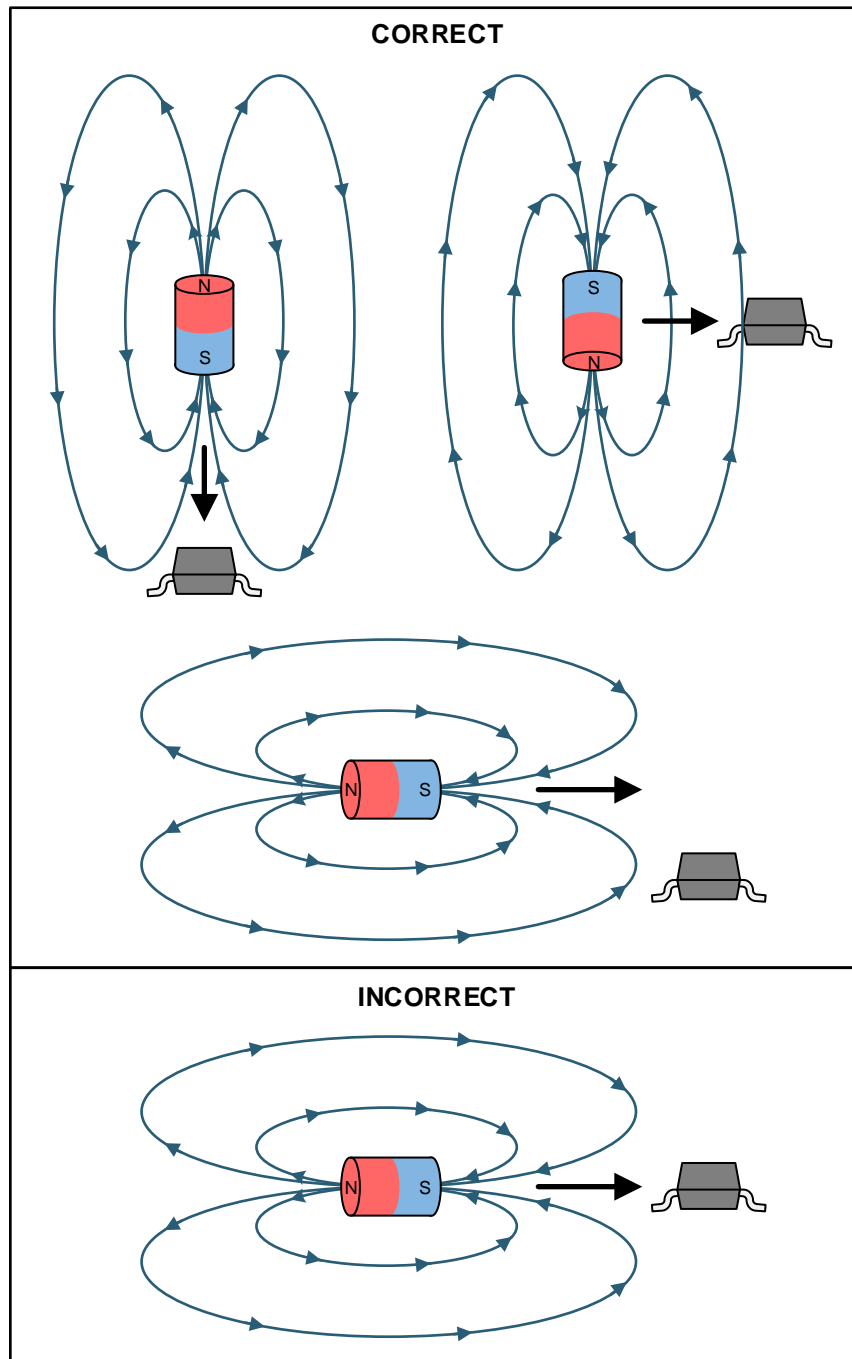


图 16. Correct and Incorrect Magnet Approaches



## 9 Power Supply Recommendations

A decoupling capacitor close to the device must be used to provide local energy with minimal inductance. TI recommends using a ceramic capacitor with a value of at least 0.01  $\mu\text{F}$ .

## 10 Layout

### 10.1 Layout Guidelines

Magnetic fields pass through most nonferromagnetic materials with no significant disturbance. Embedding Hall effect sensors within plastic or aluminum enclosures and sensing magnets on the outside is common practice. Magnetic fields also easily pass through most printed-circuit boards, which makes placing the magnet on the opposite side possible.

### 10.2 Layout Examples

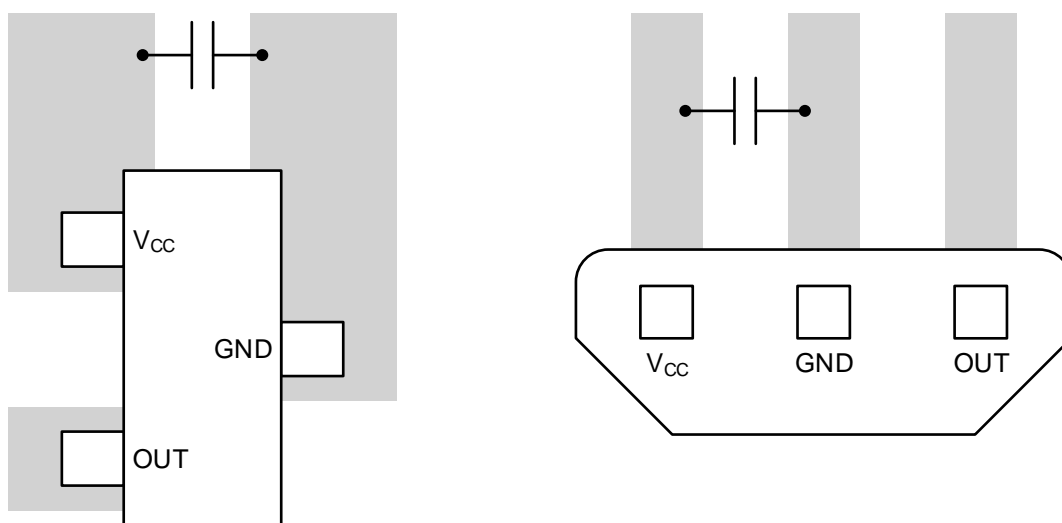


图 17. Layout Examples

## 11 器件和文档支持

### 11.1 文档支持

#### 11.1.1 相关文档

如需相关文档，请参阅：

- [《利用线性霍尔效应传感器测量角度》](#)
- [《增量旋转编码器设计注意事项》](#)

### 11.2 接收文档更新通知

要接收文档更新通知，请导航至 [TI.com](#) 上的器件产品文件夹。请单击右上角的 [提醒我](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

### 11.3 社区资源

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**设计支持** [TI 参考设计支持](#) 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

### 11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知和修订此文档。如欲获取此数据表的浏览器版本，请参阅左侧的导航。

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV5055A1QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A1	<a href="#">Samples</a>
DRV5055A1QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A1	<a href="#">Samples</a>
DRV5055A1QLPG	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A1	<a href="#">Samples</a>
DRV5055A1QLPGM	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A1	<a href="#">Samples</a>
DRV5055A2QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A2	<a href="#">Samples</a>
DRV5055A2QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A2	<a href="#">Samples</a>
DRV5055A2QLPG	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A2	<a href="#">Samples</a>
DRV5055A2QLPGM	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A2	<a href="#">Samples</a>
DRV5055A3QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A3	<a href="#">Samples</a>
DRV5055A3QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A3	<a href="#">Samples</a>
DRV5055A3QLPG	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A3	<a href="#">Samples</a>
DRV5055A3QLPGM	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A3	<a href="#">Samples</a>
DRV5055A4QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A4	<a href="#">Samples</a>
DRV5055A4QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55A4	<a href="#">Samples</a>
DRV5055A4QLPG	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A4	<a href="#">Samples</a>
DRV5055A4QLPGM	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	55A4	<a href="#">Samples</a>
DRV5055Z1QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z1	<a href="#">Samples</a>
DRV5055Z1QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z1	<a href="#">Samples</a>
DRV5055Z2QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z2	<a href="#">Samples</a>
DRV5055Z2QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z2	<a href="#">Samples</a>

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV5055Z3QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z3	<a href="#">Samples</a>
DRV5055Z3QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z3	<a href="#">Samples</a>
DRV5055Z4QDBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z4	<a href="#">Samples</a>
DRV5055Z4QDBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	55Z4	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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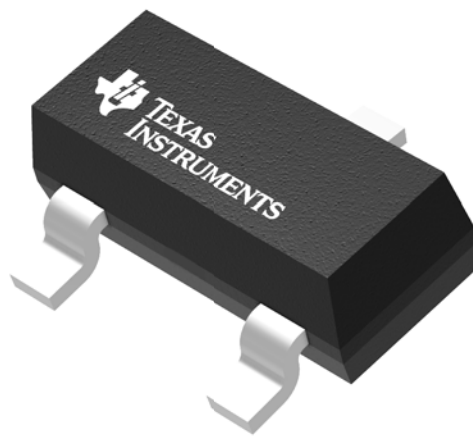
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## GENERIC PACKAGE VIEW

**DBZ 3**

**SOT-23 - 1.12 mm max height**

SMALL OUTLINE TRANSISTOR



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4203227/C

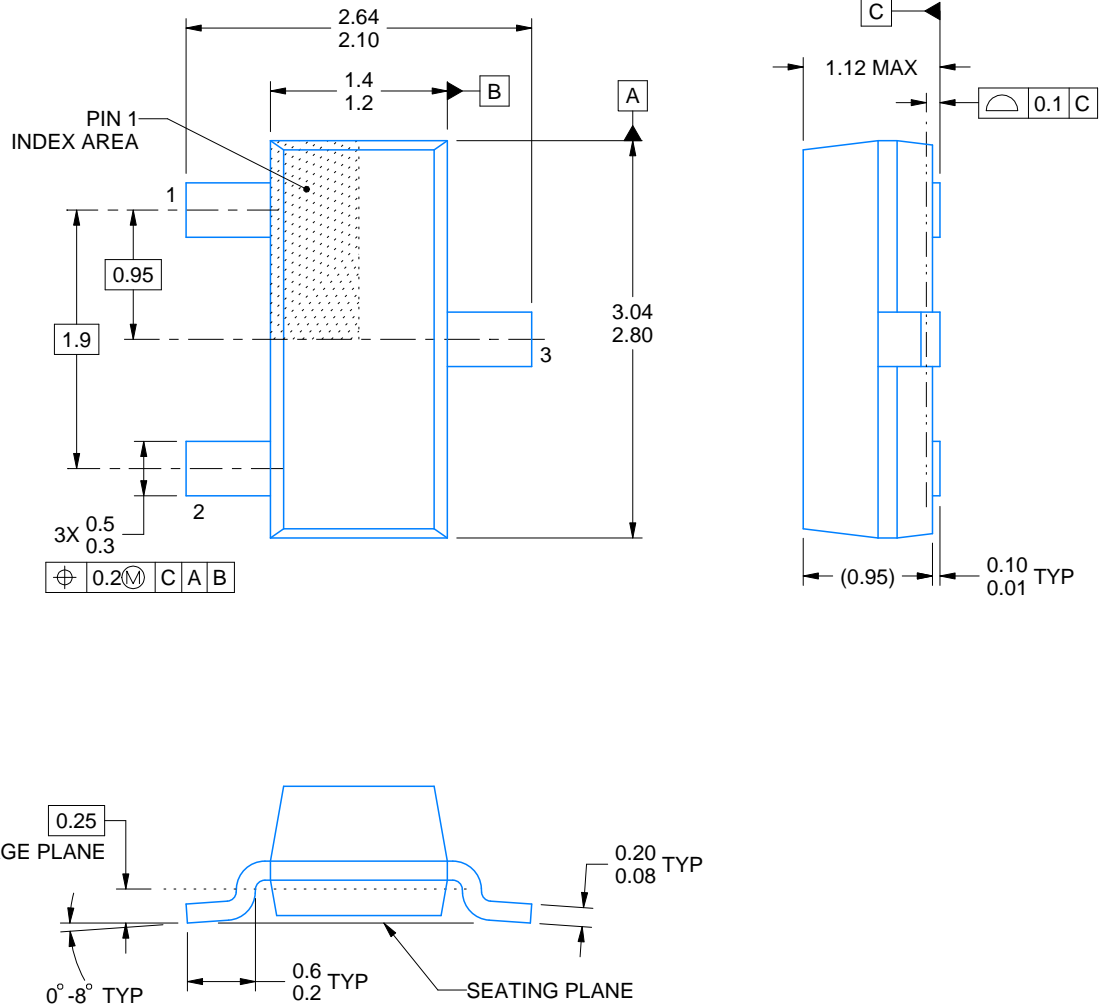
DBZ0003A



## PACKAGE OUTLINE

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



4214838/C 04/2017

### NOTES:

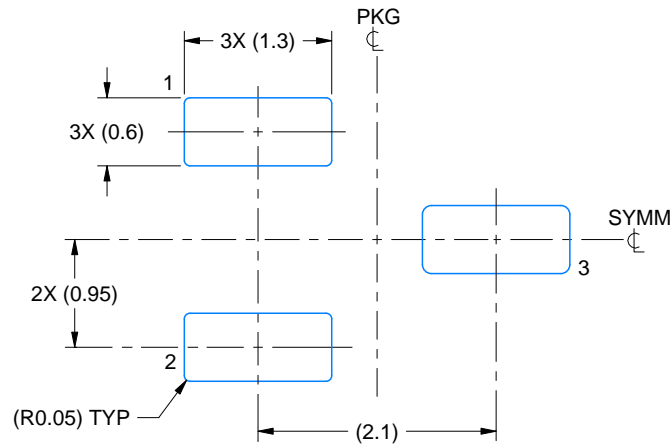
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-236, except minimum foot length.

# EXAMPLE BOARD LAYOUT

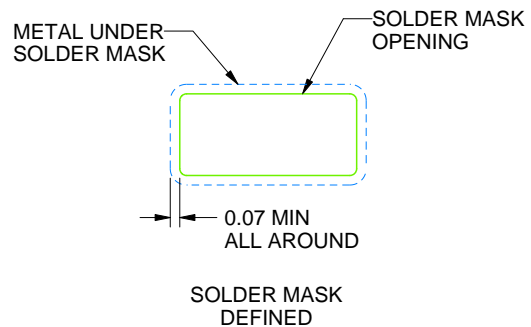
DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
SCALE:15X



SOLDER MASK DETAILS

4214838/C 04/2017

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

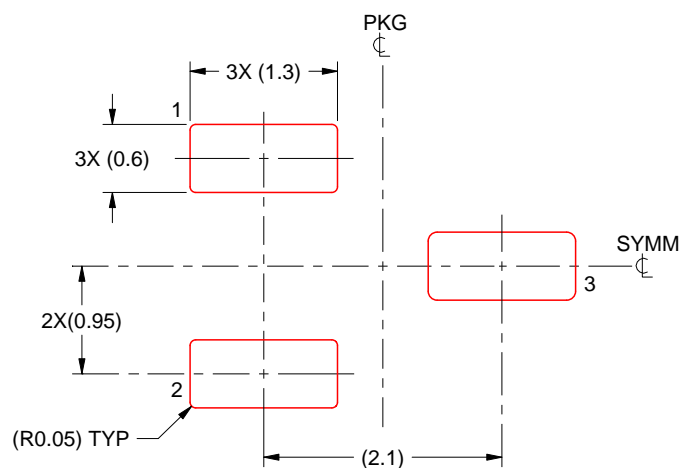


## EXAMPLE STENCIL DESIGN

DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR

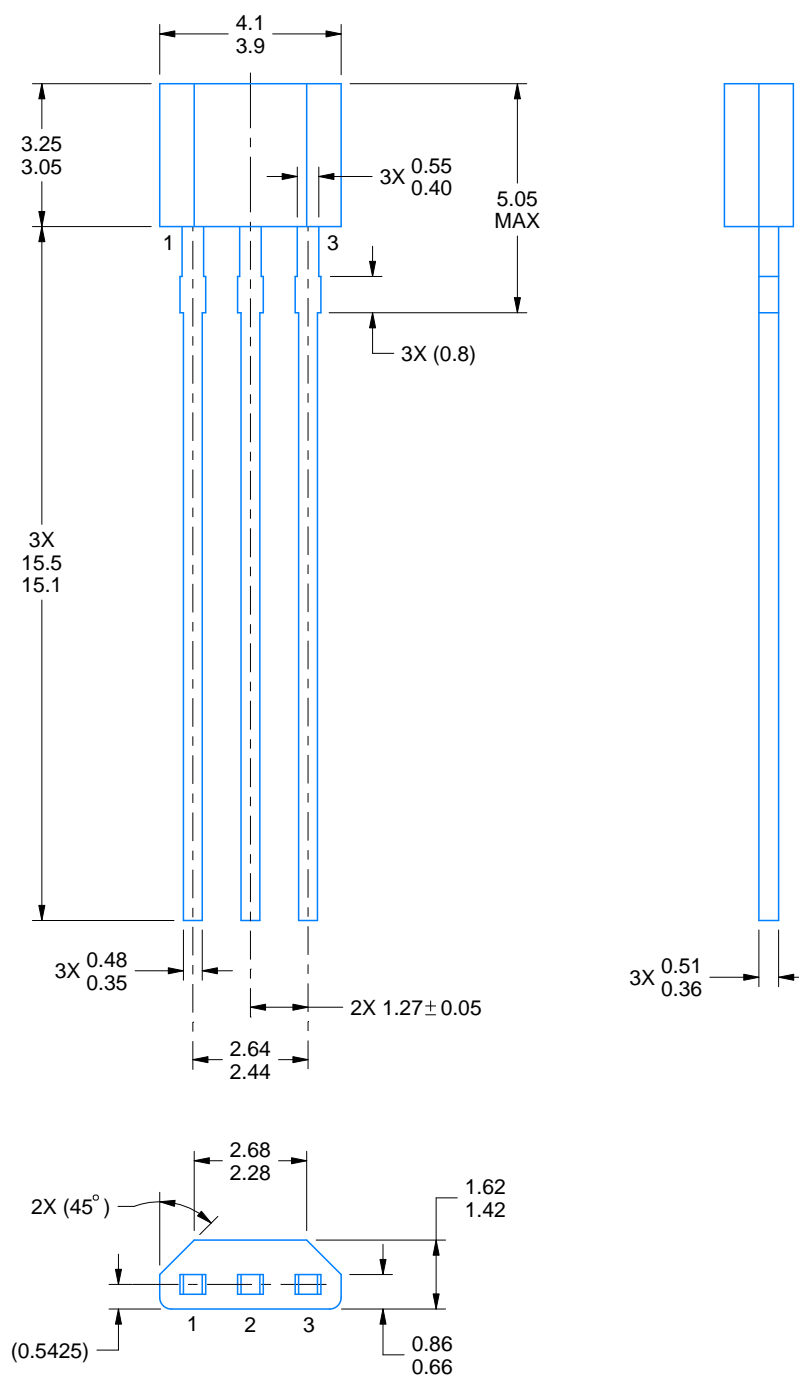
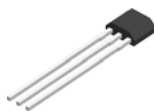


SOLDER PASTE EXAMPLE  
BASED ON 0.125 THICK STENCIL  
SCALE:15X

4214838/C 04/2017

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.



4221343/C 01/2018

## NOTES:

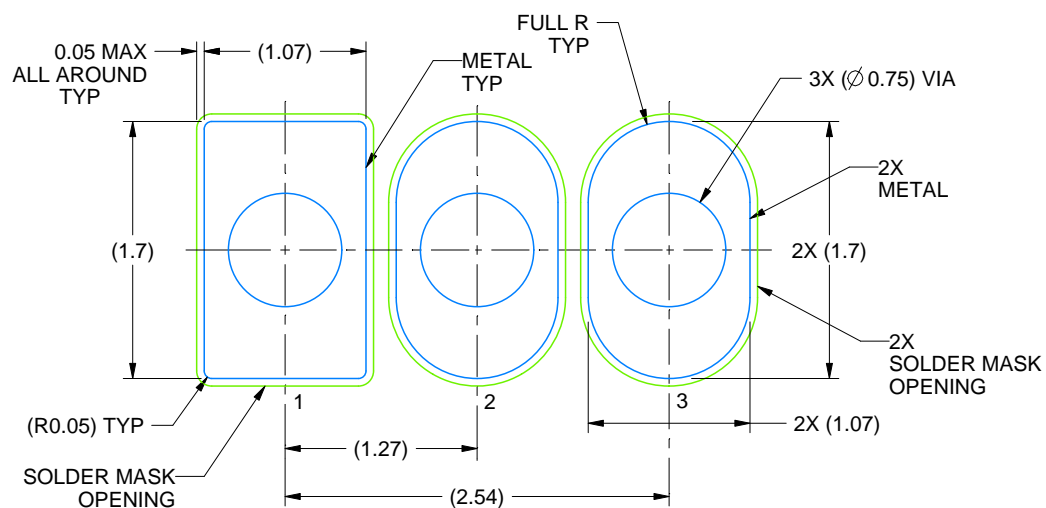
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

LPG0003A

TO-92 - 5.05 mm max height

TRANSISTOR OUTLINE



LAND PATTERN EXAMPLE  
NON-SOLDER MASK DEFINED  
SCALE:20X

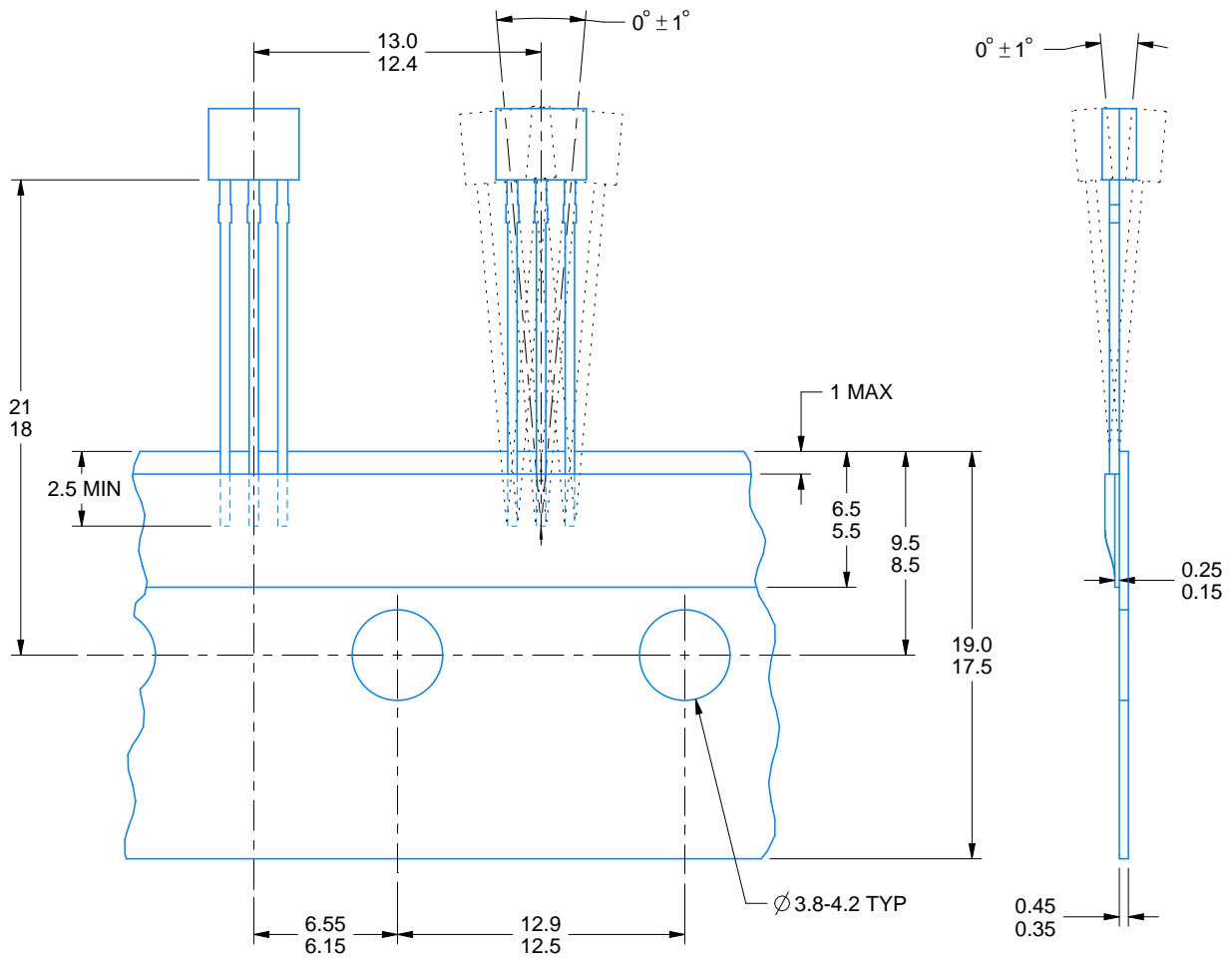
4221343/C 01/2018

# TAPE SPECIFICATIONS

LPG0003A

TO-92 - 5.05 mm max height

TRANSISTOR OUTLINE



4221343/C 01/2018

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